

SILICON DIODES

ITT SEMICONDUCTORS

87 DE 4684955 0002326 4

General Purpose and Switching Diodes in DO-35 Package

Type	Peak Inv. Voltage PIV	Max. Aver. Rectified Current I_0	Power Dissipation at 25°C	Junction Temperature T_J	Forward Voltage Drop V_F	Reverse Current I_R		Reverse Recovery Time		Conditions
						at I_F	at V_R	t_{rr} ns		
	Volts	mA	max. mW	max. °C	max. V	mA	max. nA	Volts		
BA170	20	150	300	150	1.0	80	50	10	100	$I_F = I_R = 10$ mA, to $I_R = 1$ mA
BA201	50	150	500	150	1.2	100	100	30	4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
BAV17	25	200	400	175	1.0	100	100	20	max. 50	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$ to $I_R = 3$ mA
BAV18	60	200	400	175	1.0	100	100	50	max. 50	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$ to $I_R = 3$ mA
BAV19	120	200	400	175	1.0	100	100	100	max. 50	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$ to $I_R = 3$ mA
BAV20	200	200	400	175	1.0	100	100	150	max. 50	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$ to $I_R = 3$ mA
BAV21	250	200	400	175	1.0	100	100	200	max. 50	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$ to $I_R = 3$ mA
BAW75	35	150	500	200	1.0	30	100	25	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ to $I_R = 1$ mA
BAW76	75	150	500	200	1.0	100	100	50	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ to $I_R = 1$ mA
BAX13	50	48	500	200	1.53	75	200	50	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ to $I_R = 1$ mA
BAX16	165	200	400	175	1.3	100	100	150	max. 120	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$, to $I_R = 3$ mA
BAY80	150	100	400	175	1.0	100	100	120	max. 50	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$, to $I_R = 3$ mA
ITT600	75	200	500	200	1.0	200	100	50	max. 4.0	$I_F = I_R = 10$ to 200 mA, to 0.1 I_F
ITT601	50	200	500	200	1.0	400	100	30	max. 6.0	$I_F = I_R = 10$ to 200 mA, to 0.1 I_F
ITT2001	100	150	300	175	1.0	100	100	50	50	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$, to $I_R = 3$ mA
ITT2002	200	150	300	175	1.0	100	100	150	50	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$, to $I_R = 3$ mA
ITT2003	250	150	300	175	1.0	100	100	150	50	$I_F = I_R = 30$ mA, $R_L = 100 \Omega$, to $I_R = 3$ mA
ITT3001	70	100	250	175	1.0	100	25	60	--	--
ITT3002	150	100	250	175	1.0	100	1.0	125	--	--
ITT3003	200	100	250	175	1.0	100	25	175	--	--
WG713	35	100	400	--	1.0	100	100	30	6.0	$I_F = I_R = 10$ mA, to $I_R = 10$ mA
WG1010A	15	5.0	400	--	1.0	50	1000	10	--	--
1N456A	30	150	400	175	1.0	100	25	25	--	--
1N457	60	150	400	175	1.0	20	25	60	--	--
1N458A	150	150	400	175	1.0	100	25	125	--	--
1N459A	200	150	400	175	1.0	100	25	175	--	--
1N483A	70	150	400	175	1.0	100	25	60	--	--
1N483B	80	150	400	175	1.0	100	25	60	--	--
1N484A	150	150	400	175	1.0	100	25	125	--	--
1N484B	150	150	400	175	1.0	100	250	125	--	--
1N485	200	150	400	175	1.0	100	250	175	--	--
1N485A	200	150	400	175	1.0	100	25	175	--	--
1N485B	200	150	400	175	1.0	100	25	175	--	--
1N486	250	150	400	175	1.1	100	250	225	--	--
1N486B	250	150	400	175	1.1	100	25	225	--	--
1N914	100	75	500	200	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N916	100	75	500	200	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4148*	100	150	500	200	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4149*	100	150	500	200	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4150*	50	200	500	200	1.0	200	100	50	max. 4.0	$I_F = I_R = 10$ to 200 mA, to 0.1 I_F
1N4151*	75	150	500	200	1.0	50	50	50	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4152*	40	150	400	175	0.55	0.10	50	30	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4153*	75	150	400	175	0.55	0.10	50	50	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4154*	35	150	500	200	1.0	30	100	25	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4305	75	150	400	175	0.58	0.25	100	50	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4446*	100	150	500	200	1.0	20	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4447*	100	150	500	200	1.0	20	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4448*	100	150	500	200	1.0	100	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4449*	100	150	500	200	1.0	100	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4450*	40	150	400	175	0.54	0.50	50	30	max. 4.0	$I_F = I_R = 10$ mA, to $I_R = 1$ mA
1N4451*	40	150	400	175	0.50	0.10	50	30	max. 10	$I_F = I_R = 10$ mA, to $I_R = 1$ mA
1N4453*	30	150	400	175	0.55	0.01	50	20	--	--
1N4454*	75	150	400	175	1.0	10	100	50	max. 4.0	$I_F = I_R = 10$ mA, to $I_R = 1$ mA

The following types are also available to specification CECC 50001-024: BAV17, BAV18, BAV19, BAV20 and BAV21.

The following types are also available to specification CECC 50001-023: 1N4148, 1N4149, 1N4447, 1N4448 and 1N4449.

*During 1987, branding of these diodes will be changed from letters to the international color code.